

NCE N-Channel **Super Trench II** Power MOSFET

Description

The NCEP011NH25QU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

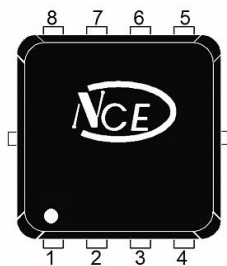
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

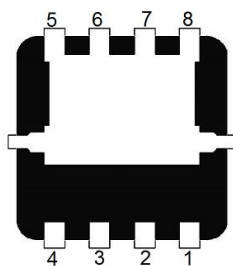
- $V_{DS} = 25V, I_D = 161A$
 - $R_{DS(ON)} = 1.1m\Omega$ (typical) @ $V_{GS} = 10V$
 - $R_{DS(ON)} = 1.8m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150°C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔV_{ds} TESTED!

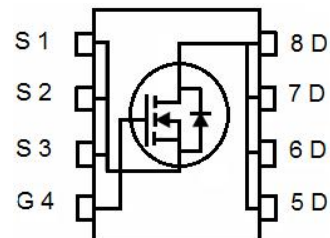
PDFN 3.3X3.3-8L



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP011NH25QU	NCEP011NH25QU	PDFN3.3X3.3-8L	Ø330mm	12mm	5000units

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	161	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	102	A
Pulsed Drain Current	I_{DM}	644	A
Maximum Power Dissipation	P_D	69	W
Derating factor		0.55	W/ $^\circ C$
Single pulse avalanche energy ^(Note 1)	E_{AS}	540	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.81	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	25	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =25V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	1.1	1.65	mΩ
		V _{GS} =4.5V, I _D =20A	-	1.8	2.75	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =30A	-	50	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2900	-	pF
Output Capacitance	C _{oss}		-	805	-	pF
Reverse Transfer Capacitance	C _{rss}		-	80	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =20A V _{GS} =10V, R _G =1.6Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	7	-	nS
Turn-Off Delay Time	t _{d(off)}		-	35	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =20A, V _{GS} =10V	-	40	-	nC
Gate-Source Charge	Q _{gs}		-	9.2		nC
Gate-Drain Charge	Q _{gd}		-	5.0		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current	I _S		-	-	161	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =100A	-	22	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs	-	40	-	nC

Notes:

1. EAS condition : T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

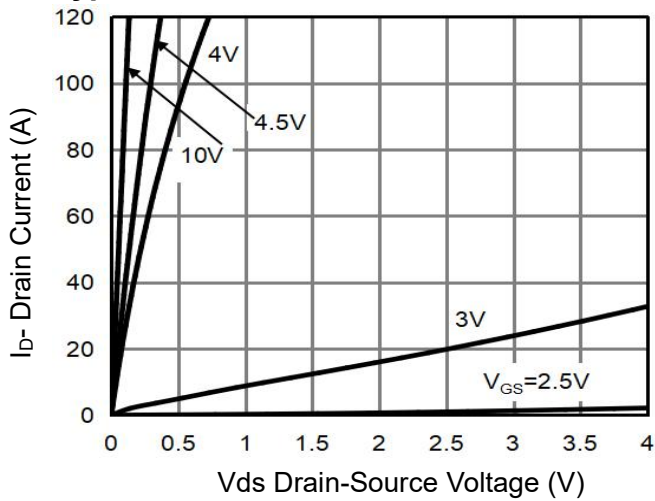


Figure 1 Output Characteristics

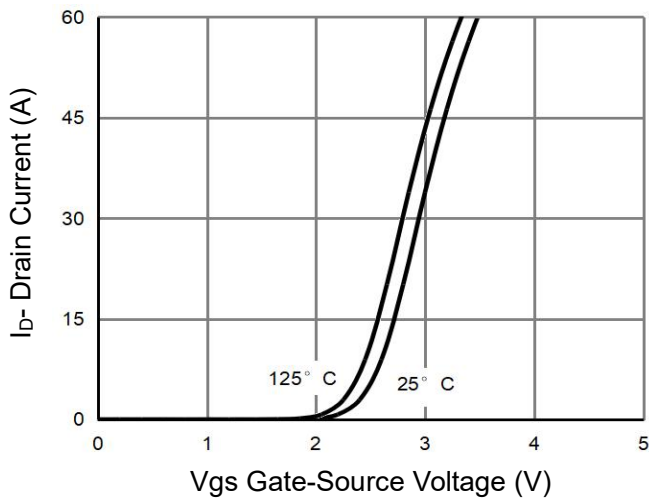


Figure 2 Transfer Characteristics

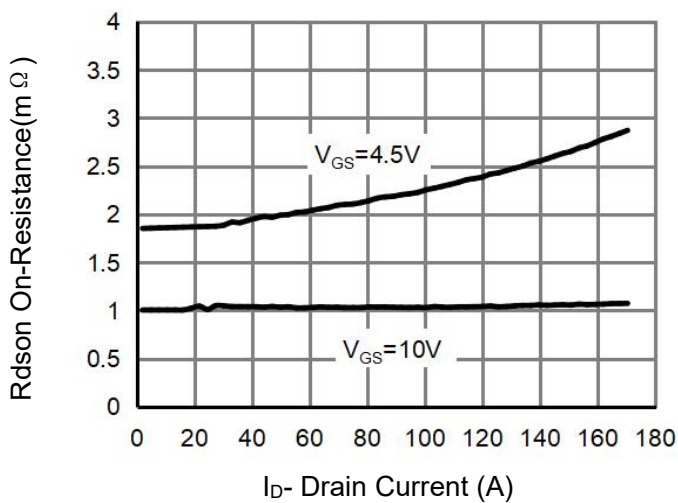


Figure 3 Rdson- Drain Current

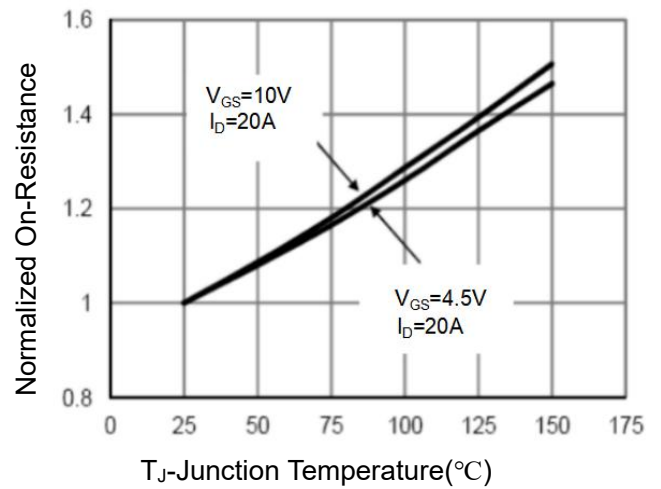


Figure 4 Rdson-Junction Temperature

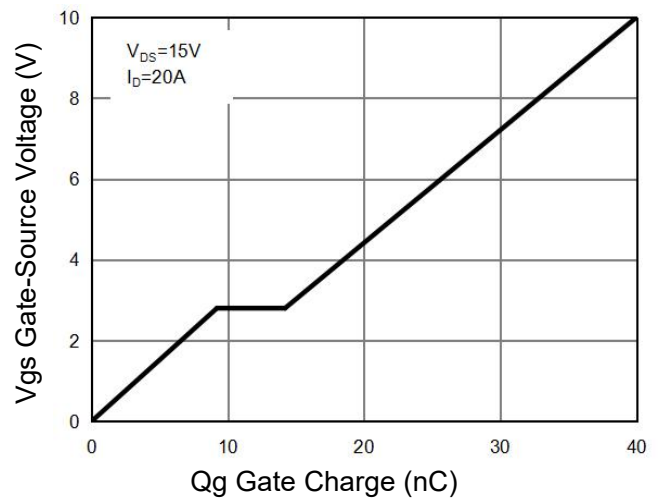


Figure 5 Gate Charge

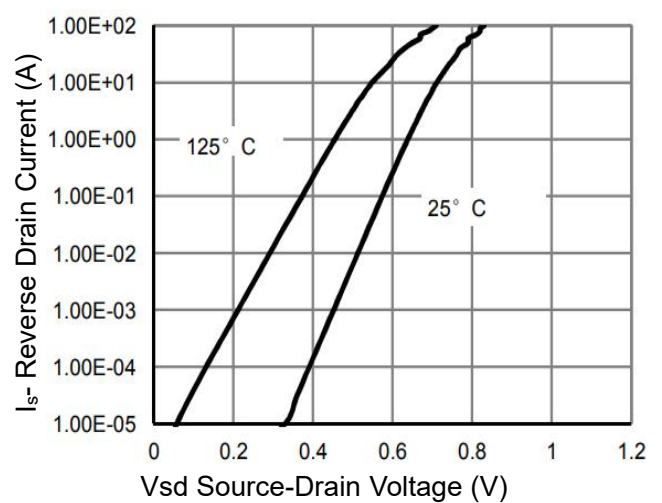


Figure 6 Source- Drain Diode Forward

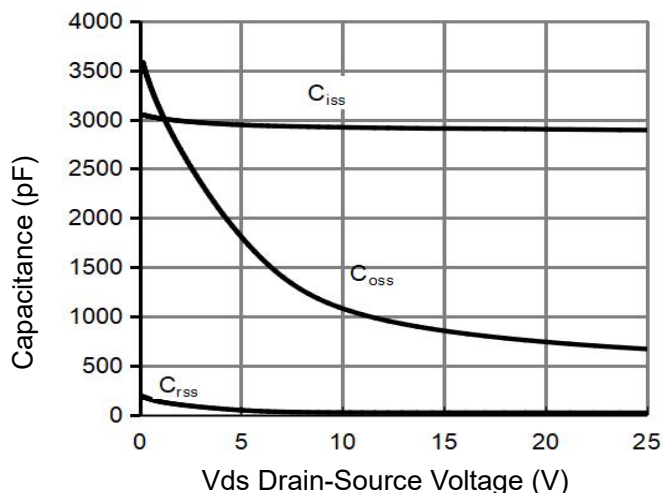


Figure 7 Capacitance vs Vds

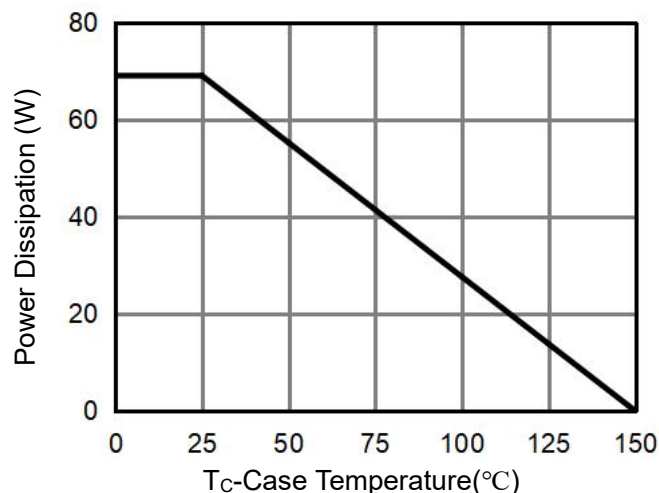


Figure 9 Power De-rating

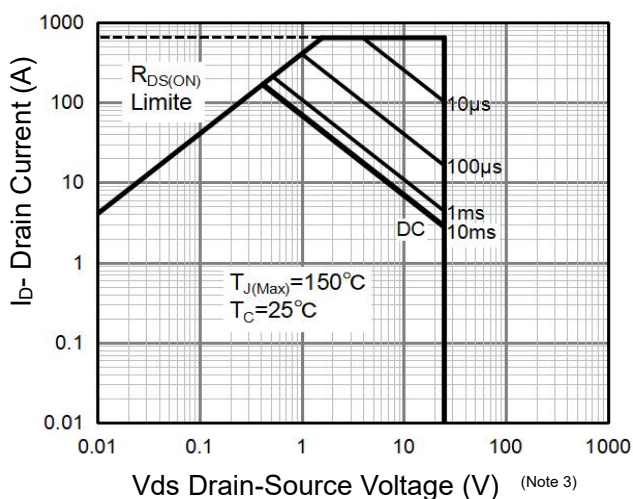


Figure 8 Safe Operation Area

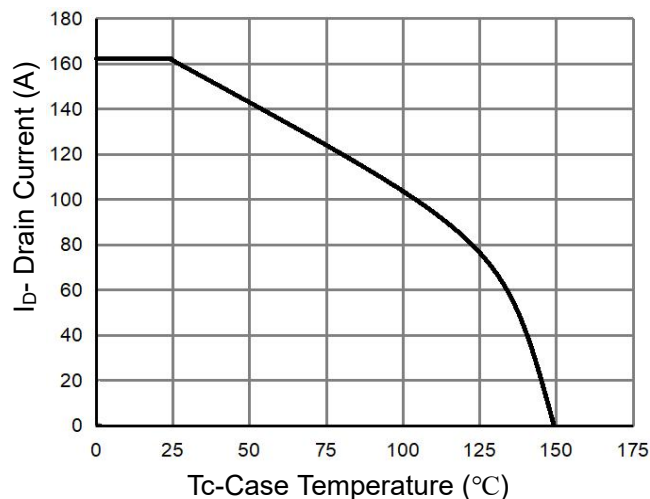


Figure 10 Current De-rating

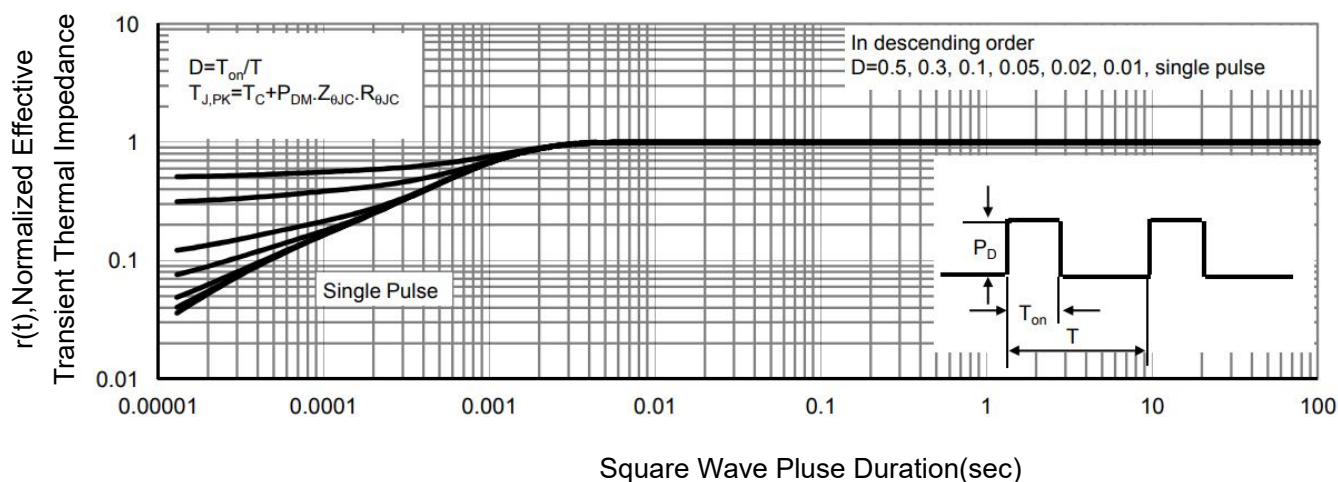
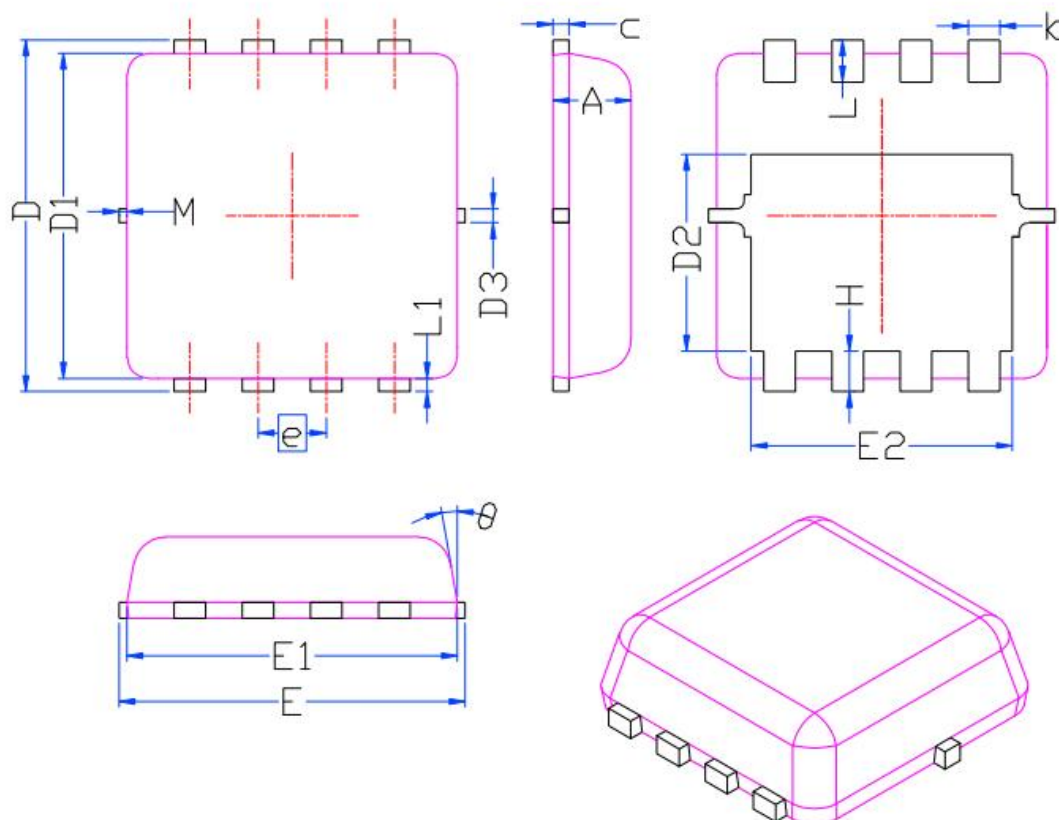


Figure 11 Normalized Maximum Transient Thermal Impedance

PDFN3.3X3.3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	-	0.13	-
E	3.10	3.20	3.30
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

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